

L Number	Hits	Search Text	DB	Time Stamp
26	7513	(soi or (semiconductor adj on adj insulat\$3)) near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 18:29
27	100	(silicon near2 carbide) near2 boat	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 18:30
28	2	((soi or (semiconductor adj on adj insulat\$3)) near2 substrate) same ((silicon near2 carbide) near2 boat)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 18:30
	34	silicon adj boat	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 18:41
	34	silicon adj boat	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 11:08
	60174	silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 18:18
	92082	cvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 18:18
	2120	(silicon adj carbide) same cvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 18:18
	66246	boat	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 18:18
	41	((silicon adj carbide) same cvd) same boat	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 18:18
	34	silicon adj boat	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 19:44
	1	((silicon adj carbide) same cvd) same boat) and (silicon adj boat)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 18:43
	74	((silicon adj carbide) same cvd) same boat) or (silicon adj boat)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 18:43
	14400	soi	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 19:43

34	silicon adj boat	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/21 19:44
1	soi same (silicon adj boat)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/21 19:46
1146922	semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/21 19:50
5	(silicon adj boat) same semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/21 19:46
12	semiconductor adj on adj insulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/07 18:28
14562	soi	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/02 11:04
508529	transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/02 11:04
3801	soi same transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/02 11:04
60532	silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/02 11:04
10	(soi same transistor) same (silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/07 18:28
15468	soi or (silicon near2 insulator)	USPAT; US-PGPUB	2003/05/18 20:25
265	silicon near2 boat	USPAT; US-PGPUB	2003/05/18 20:25
14	(soi or (silicon near2 insulator)) and (silicon near2 boat)	USPAT; US-PGPUB	2003/05/18 20:26
13	((soi or (silicon near2 insulator)) and (silicon near2 boat)) and @ad<20020307	USPAT; US-PGPUB	2003/05/18 20:27
1	("6468884").PN.	USPAT; US-PGPUB	2003/10/29 10:53
4619	((438/149) or (438/311) or (438/459) or (438/584) or (438/706) or (438/758) or (438/795) or (438/909) or (438/935)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/07 14:18
405	(silicon or ((single near2 crystal) adj silicon) or (poly near2 silicon) or (silicon near2 carbide)) near2 boat	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/07 14:33

20	((438/149) or (438/311) or (438/459) or (438/584) or (438/706) or (438/758) or (438/795) or (438/909) or (438/935)).CCLS.) and ((silicon or ((single near2 crystal) adj silicon) or (poly near2 silicon) or (silicon near2 carbide)) near2 boat)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 14:26
100	(silicon near2 carbide) near2 boat	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 18:29
8	((438/149) or (438/311) or (438/459) or (438/584) or (438/706) or (438/758) or (438/795) or (438/909) or (438/935)).CCLS.) and ((silicon near2 carbide) near2 boat)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 14:33
0	6296709.URPN.	USPAT	2003/11/07 14:37
5	((4640223"   "4964378"   "5001327"   "5029554"   "6139642"), PN.	USPAT	2003/11/07 14:37